Bipolar Transistor (-)50 V, (-)3 A, Low V_{CE}(sat), (PNP)NPN Single

This device is bipolar junction transistor featuring high current, low saturation voltage, and high speed switching.

Suitable for motor driver, relay driver, DC-DC converter of automotive applications. AEC-Q101qualified and PPAP capable.

Features

- Large Current Capacitance
- Low Collector to Emitter Saturation Voltage
- High-Speed Switching
- High Allowable Power Dissipation
- AEC-Q101Qualified and PPAP Capable
- Pb-Free, Halogen Free and RoHS Compliance
- Ultra Small Package Facilitates Miniaturization in End Products (Mounting Height: 0.9 mm)

Typical Applications

- DC / DC Converter
- Relay Drivers, Lamp Drivers, Motor Drivers
- Flash

Specifications

ABSOLUTE MAXIMUM RATINGS at $T_A = 25$ °C

Parameter	Symbol	Value	Unit
Collector to Base Voltage	V _{CBO}	(-50) 100	V
Collector to Emitter Voltage	V _{CES}	(-50) 100	V
Collector to Emitter Voltage	V _{CEO}	(–)50	V
Emitter to Base Voltage	V _{EBO}	(-)6	V
Collector Current	I _C	(-)3	Α
Collector Current (Pulse)	I _{CP}	(-)6	Α
Base Current	Ι _Β	(-)600	mA
Collector Dissipation (Note 1)	P _C	1.1	W
Junction Temperature	Tj	175	°C
Storage Temperature	Tstg	-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

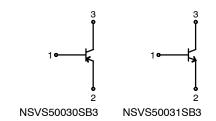
1. Surface mounted on ceramic substrate. (600 mm² x 0.8 mm)



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ELECTRICAL CONNECTION





СРН3 CASE 318BA

MARKING DIAGRAMS



XXX = HAE: NSVS50030SB3 = HCE: NSVS50031SB3

= Single Digit Date Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing) †	
NSVS50030SB3T1G	HAE	CPH3	3,000/ Tape & Reel	
NSVS50031SBST1G	HCE	(Pb-Free / Halogen Free)		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

		Conditions	Value			
Parameter	Symbol		Min	Тур	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = (-)40 V, I _E = 0 A			(-)1	μΑ
Emitter Cutoff Current	I _{EBO}	V _{EB} = (-)4 V, I _C = 0 A			(-)1	μΑ
DC Current Gain	h _{FE}	V _{CE} = (-)2 V, I _C = (-)100 mA	200		560	
Gain-Bandwidth Product	f _T	V _{CE} = (-)10 V, I _C = (-)500 mA		(360) 380		MHz
Output Capacitance	Cob	V _{CB} = (-)10 V, f = 1 MHz		(24) 13		pF
Collector to Emitter Saturation Voltage	V _{CE} (sat)	I _C = (-)1 A, I _B = (-)50 mA		(-100) 80	(-200) 120	mV
		I _C = (-)2 A, I _B = (-)100 mA		(-185) 140	(-500) 210	mV
Base to Emitter Saturation Voltage	V _{BE} (sat)	I _C = (-)2 A, I _B = (-)100 mA		(-)0.88	(-)1.2	V
Collector to Base Breakdown Voltage	V _{(BR)CBO}	$I_C = (-)10 \mu A, I_E = 0 A$	(-50) 100			V
Collector to Emitter Breakdown Voltage	V _{(BR)CES}	$I_C = (-)100 \mu A$, $R_{BE} = 0 \Omega$	(-50) 100			V
Collector to Emitter Breakdown Voltage	V _{(BR)CEO}	$I_C = (-)1 \text{ mA}, R_{BE} = \infty$	(-)50			V
Emitter to Base Breakdown Voltage	V _{(BR)EBO}	I _E = (-)10 μA, I _C = 0 A	(-)6			V
Turn-On Time	t _{on}	See Fig.1		(30) 35		ns
Storage Time	t _{stg}	7		(230) 300		ns
Fall Time	t _f			(15) 22		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

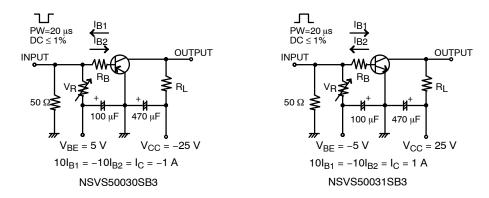


Figure 1. Switching Time Test Circuit

TYPICAL PERFORMANCE CHARACTERISTICS

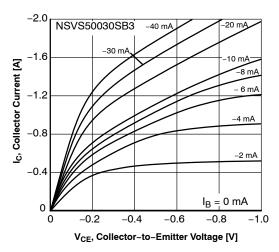


Figure 2. I_C - V_{CE}

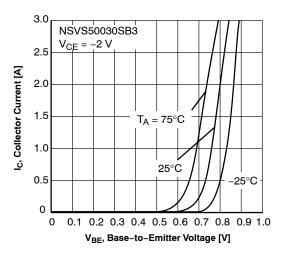


Figure 4. I_C - V_{BE}

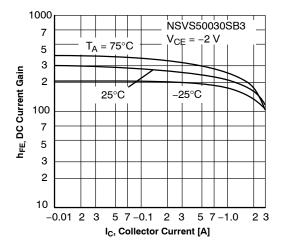


Figure 6. h_{FE} - I_C

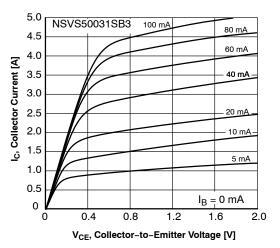


Figure 3. I_C - V_{CE}

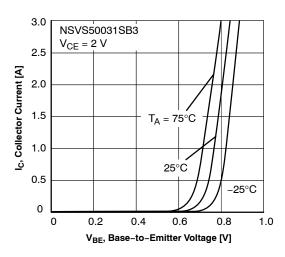


Figure 5. I_C - V_{BE}

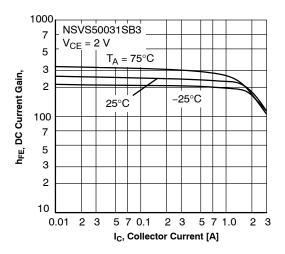


Figure 7. h_{FE} - I_C

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

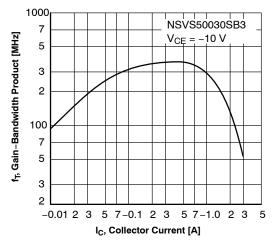


Figure 8. f_T - I_C

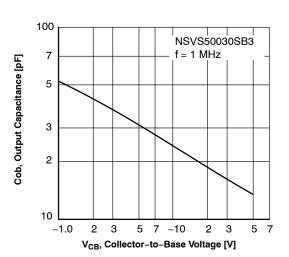


Figure 10. Cob - V_{CB}

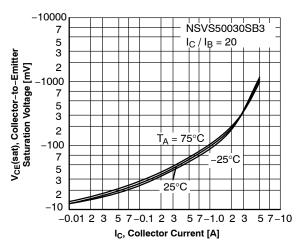


Figure 12. V_{CE}(sat) - I_C

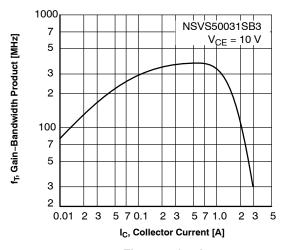


Figure 9. f_T - I_C

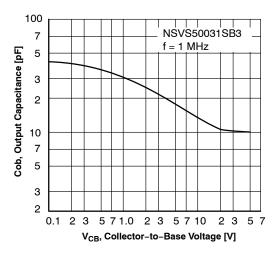


Figure 11. Cob - V_{CB}

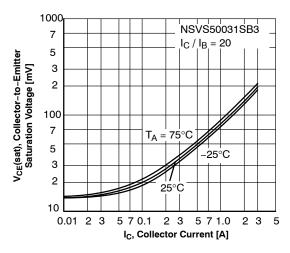


Figure 13. V_{CE}(sat) - I_C

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

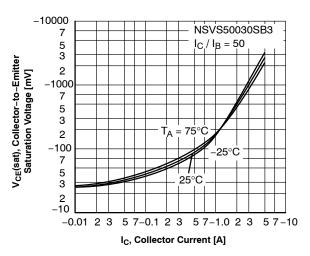


Figure 14. V_{CE}(sat) - I_C

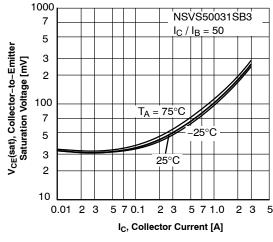


Figure 15. V_{CE}(sat) - I_C

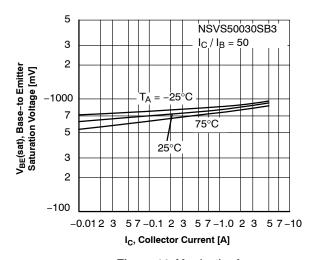


Figure 16. V_{BE}(sat) - I_C

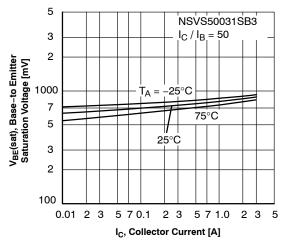


Figure 17. V_{BE}(sat) - I_C

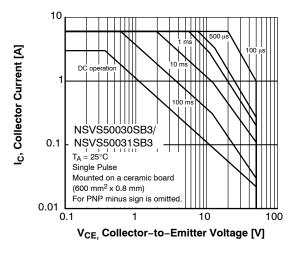


Figure 18. ASO

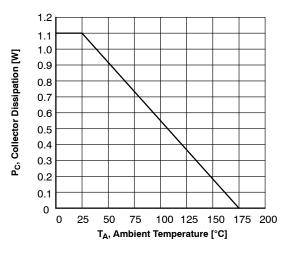
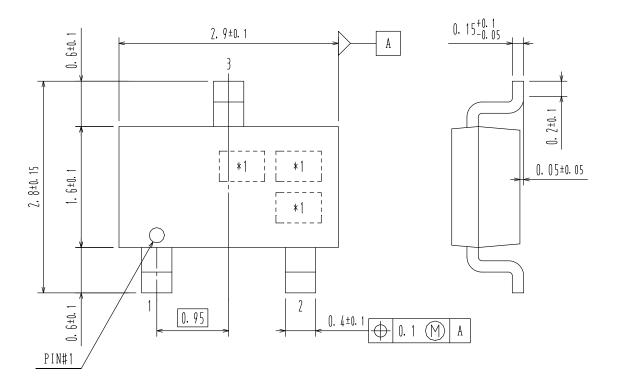
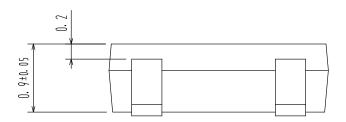


Figure 19. P_C - T_A

CPH3 CASE 318BA ISSUE O

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